

Description

The AO9926B uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.



SOP-8

General Features

 $V_{DS} = 20V I_{D} = 8 A$

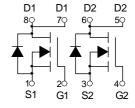
 $R_{DS(ON)} < 20m\Omega$ @ V_{GS} =4.5V

Application

Battery protection

Load switch

Uninterruptible power supply



Dual N-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
AO9926B	SOP-8	HXY MOSFET	3000

Absolute Maximum Ratings (Tc=25℃unless otherwise noted)

Symbol	Parameter	Limit	Unit
V _{DS}	Drain-Source Voltage	20	V
V _G S	Gate-Source Voltage	±12	V
I _D	Drain Current-Continuous	8	А
Ірм	Pulsed Drain Current	28	А
P _D	Maximum Power Dissipation	2.25	W
Тл,Твтв	Operating Junction and Storage Temperature Range	-55 To 150	$^{\circ}$
Rejc	Thermal Resistance,Junction-to-Case ^(Note 2)	80	°C/W



Electrical Characteristics (T_J=25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Static Characteristics	Static Characteristics					
Drain-Source Breakdown Voltage	BV _{DSS}	$V_{GS} = 0V, I_D = 250\mu A$	20	-	-	V
Gate Leakage Current	lgss	V _{GS} = ±12V, V _{DS} = 0V	-	-	±100	nA
Drain Cut-off Current	IDSS	V _{DS} = 20V, V _{GS} = 0V	-	-	1	μA
Gate Threshold Voltage	V _{GS(th)}	V _{GS} = V _{DS} , I _D = 250μA	0.45	0.7	1	٧
Drain-Source On-State Resistance ³		V _{GS} = 4.5V, I _D =5A	-	13	20	mΩ
	R _{DS(on)}	V _{GS} = 2.5V, I _D = 4.7A	-	18	30	
		V _{GS} = 1.8V, I _D = 4.3A	-	28	57	
Dynamic Characteristics ⁴						
Input Capacitance	C _{iss}	V _{GS} = 0V, V _{DS} = 10V, f = 1MHz	-	700	-	pF
Output Capacitance	C _{oss}		-	120	-	
Reverse Transfer Capacitance	Crss		-	105	-	
Switching Characteristics ⁴						
Total Gate Charge	Qg		-	10.5	-	nC
Gate-Source Charge	Qgs	V _{GS} = 4.5V, V _{DS} = 10V, I _D = 5A	-	2	-	
Gate-Drain Charge	Q _{gd}		-	2.5	-	
Turn-On Time	t _{d(on)}	V_{GS} = 5V, V_{DD} = 10V, I_D = 5A, R_G = 3 Ω ,	-	10	-	ns
Rise Time	t _r		-	20	-	
Turn-Off Time	t _{d(off)}		-	32	-	
Fall Time	tf		-	12	-	
Source-Drain Diode Characteristics						
Body Diode Voltage ³	V _{SD}	I _S =4A, V _{GS} = 0V	-	-	1.2	V
Continuous Source Current	Is		-	-	8	А

Notes:

- 1. Repetitive rating, pulse width limited by junction temperature $T_{\text{J(MAX)}}\text{=}150^{\circ}\text{C}.$
- 2. The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper, The value in any given application depends on the user's specific board design.
- 3. Pulse Test: Pulse width≤300µs, duty cycle≤2%.
- 4. This value is guaranteed by design hence it is not included in the production test.



Typical Characteristics

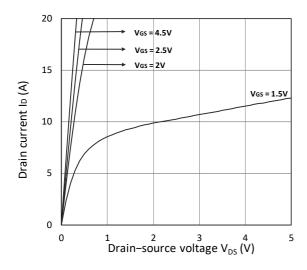


Figure 1. Output Characteristics

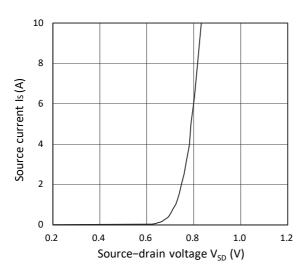


Figure 3. Forward Characteristics of Reverse

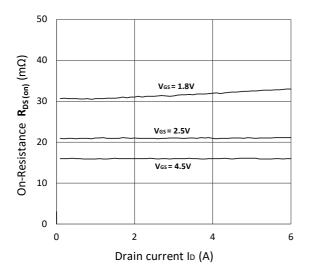


Figure 5. $R_{DS(ON)}$ vs. I_D

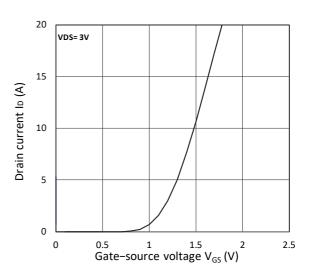


Figure 2. Transfer Characteristics

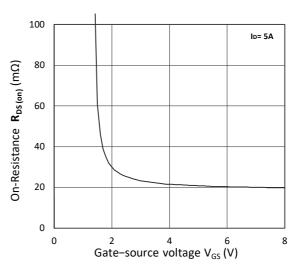


Figure 4. $R_{DS(ON)}$ vs. V_{GS}

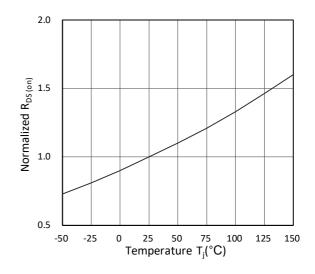
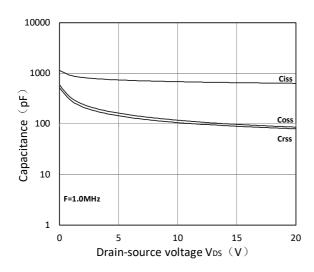


Figure 6. Normalized $R_{\text{DS(on)}}$ vs. Temperature





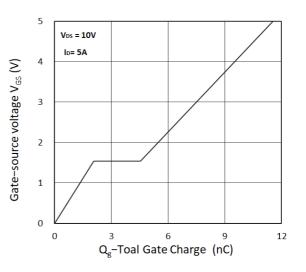
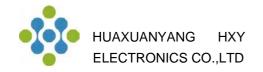
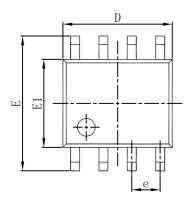
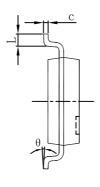


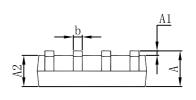
Figure 8. Gate Charge Characteristics



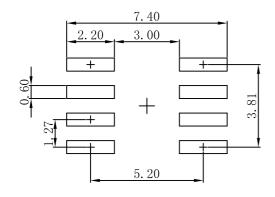
SOP-8 Package Outline Dimensions







Symbol	Dimensions In Millimeters		Dimensions In Inches			
	Min	Max	Min	Max		
A	1.350	1.750	0.053	0.069		
A1	0.100	0.250	0.004	0.010		
A2	1.350	1.550	0.053	0.061		
b	0.330	0.510	0.013	0.020		
c	0.170	0.250	0.007	0.010		
D	4.800	5.000	0.189	0. 197		
e	1. 270 (1.270 (BSC)		0.050 (BSC)		
E	5.800	6. 200	0. 228	0.244		
E1	3.800	4.000	0.150	0. 157		
L	0.400	1.270	0.016	0.050		
θ	0°	8°	0°	8°		



- Note: 1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
 3.The pad layout is for reference purposes only.



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